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January 2016

FQP3P50

P-Channel QFET® MOSFET

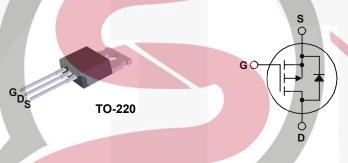
-500 V, -2.7 A, 4.9 Ω

Description

This P-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance • Low Crss (Typ 9.5 pF) and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, • 100% Avalanche Tested DC motor control, and variable switching power applications.

Features

- -2.7 A, -500 V, $R_{DS(on)}$ = 4.9 Ω (Max.) @ V_{GS} = -10 V, $I_D = -1.35 A$
- Low Gate Charge (Typ. 18 nC)



Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FQP3P50	Unit	
V _{DSS}	Drain-Source Voltage		-500	V	
I _D	Drain Current - Continuous (T _C = 25°C)		-2.7	Α	
	- Continuous (T _C = 100°C)		-1.71	Α	
I _{DM}	Drain Current - Pulsed	(Note 1)	-10.8	A	
V _{GSS}	Gate-Source Voltage		± 30	V	
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	250	mJ	
I _{AR}	Avalanche Current	(Note 1)	-2.7	Α	
E _{AR}	Repetitive Avalanche Energy	(Note 1)	8.5	mJ	
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	-4.5	V/ns	
P _D	Power Dissipation (T _C = 25°C)		85	W	
- Derate above 25°C			0.68	W/°C	
T_J , T_{STG}	T _{STG} Operating and Storage Temperature Range		-55 to +150	°C	
T _I	Maximum lead temperature for soldering,		300	°C	
·L	1/8" from case for 5 seconds	300			

Thermal Characteristics

Symbol	Parameter	FQP3P50	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	1.47	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W

Package	Marking	and	Ordering	Information
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Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQP3P50	FQP3P50	TO-220	Tube	N/A	N/A	50 units

Elerical Characteristics

 $T_C = 25$ °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Мах.	Unit
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	-500			V
ΔBV_{DSS} / ΔT_{J}	Breakdown Voltage Temperature Coefficient	I_D = -250 μ A, Referenced to 25°C		0.42		V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -500 V, V _{GS} = 0 V			-1	μΑ
	Zero Gate Voltage Drain Current	$V_{DS} = -400 \text{ V}, T_{C} = 125 ^{\circ}\text{C}$		/	-10	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = -30 \text{ V}, V_{DS} = 0 \text{ V}$		4	-100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = 30 \text{ V}, V_{DS} = 0 \text{ V}$		7/	100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$	-3.0		-5.0	V

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$	-3.0		-5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = -10 V, I _D = -1.35 A	/	3.9	4.9	Ω
9 _{FS}	Forward Transconductance	$V_{DS} = -50 \text{ V}, I_{D} = -1.35 \text{ A}$		2.35		S

Dynamic Characteristics

C _{iss}	Input Capacitance	$V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V},$	\	510	660	pF
Coss	Output Capacitance	f = 1.0 MHz		70	90	pF
C _{rss}	Reverse Transfer Capacitance			9.5	12	pF

Switching Characteristics

	3		- /				
t _{d(on)}	Turn-On Delay Time	$V_{DD} = -250 \text{ V}, I_{D} = -2.7 \text{ A},$	4		12	35	ns
t _r	Turn-On Rise Time	$R_G = 25 \Omega$			56	120	ns
t _{d(off)}	Turn-Off Delay Time				35	80	ns
t _f	Turn-Off Fall Time	(No	ote 4)		45	100	ns
Q_g	Total Gate Charge	$V_{DS} = -400 \text{ V}, I_{D} = -2.7 \text{ A},$			18	23	nC
Q _{gs}	Gate-Source Charge	V _{GS} = -10 V		/	3.6		nC
Q _{gd}	Gate-Drain Charge	(No	te 4)	/	9.2		nC

Drain-Source Diode Characteristics and Maximum Ratings

IS		Maximum Continuous Drain-Source Did	ode Forward Current			-2.7	А
I _{SM}		Maximum Pulsed Drain-Source Diode F	Forward Current			-10.8	Α
V _{SD}	1	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V, } I_{S} = -2.7 \text{ A}$			-5.0	V
t _{rr}		Reverse Recovery Time	V _{GS} = 0 V, I _S = -2.7 A,	D	270	F 4	ns
Q _{rr}		Reverse Recovery Charge	dl _F / dt = 100 A/μs	D-1	1.5		μC

- 1. Repetitive rating : pulse-width limited by maximum junction temperature.
- 2. L = 62 mH, I $_{AS}$ = -2.7 A, V $_{DD}$ = -50 V, R $_{G}$ = 25 Ω , starting T $_{J}$ = 25°C. 3. I $_{SD}$ \leq -2.7 A, di/dt \leq 200 A/ μs , V $_{DD}$ \leq BV $_{DSS}$, starting T $_{J}$ = 25°C.
- 4. Essentially independent of operating temperature.

Typical Characteristics

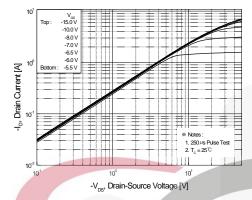


Figure 1. On-Region Characteristics

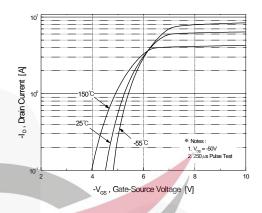


Figure 2. Transfer Characteristics

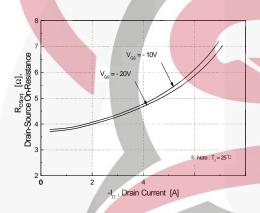


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage



Figure 4. Body Diode Forward Voltage
Variation vs. Source Current
and Temperature

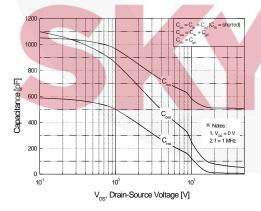


Figure 5. Capacitance Characteristics

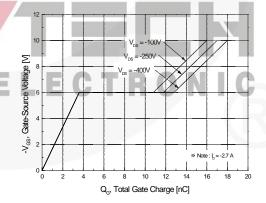
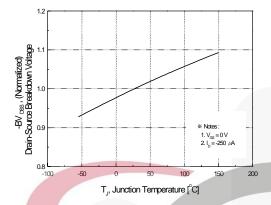


Figure 6. Gate Charge Characteristics

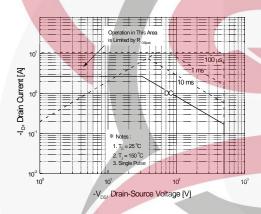
Typical Characteristics (Continued)



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Figure 7. Breakdown Voltage Variation vs. Temperature

Figure 8. On-Resistance Variation vs. Temperature



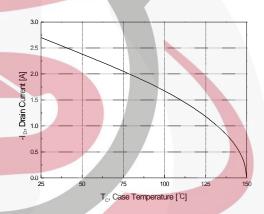


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature

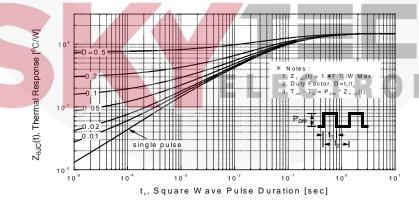
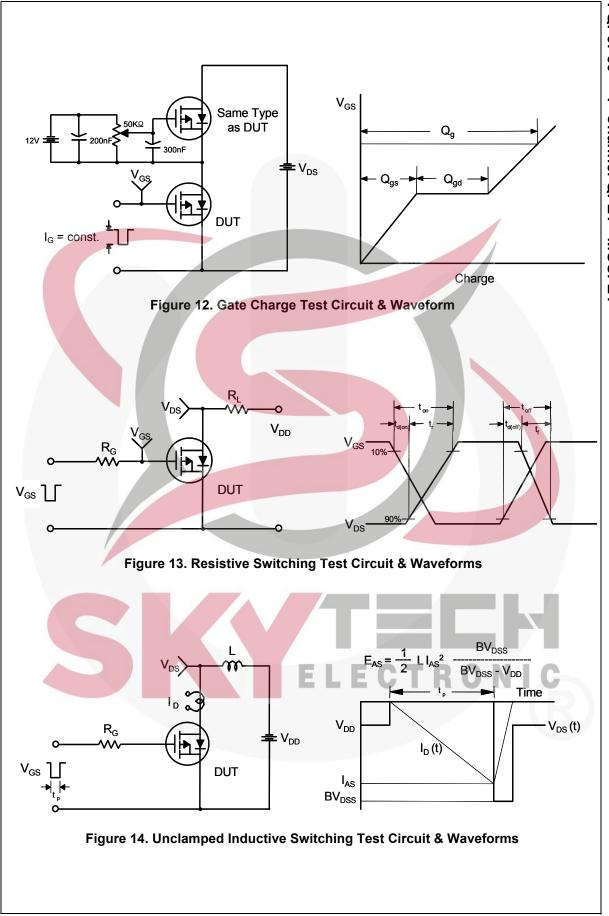
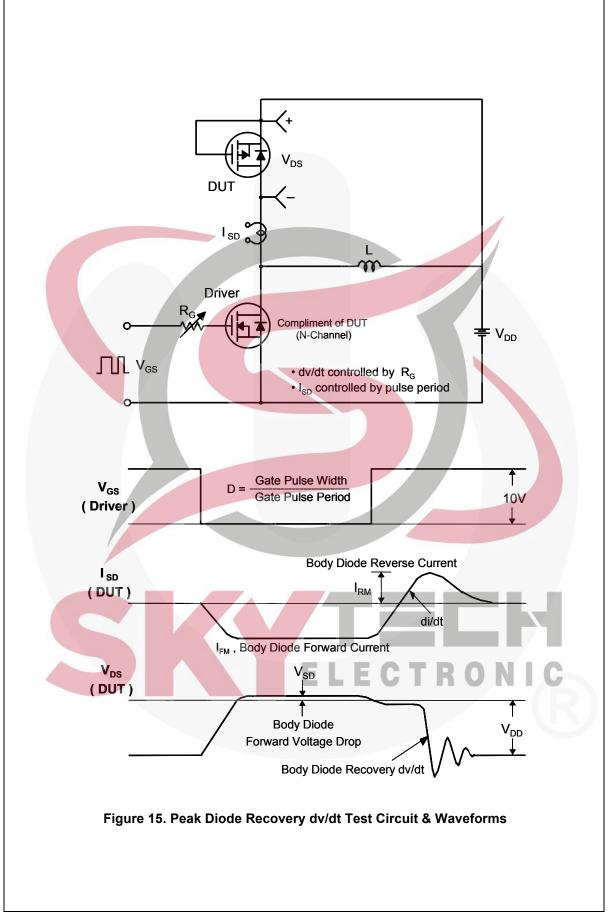


Figure 11. Transient Thermal Response Curve







Mechanical Dimensions

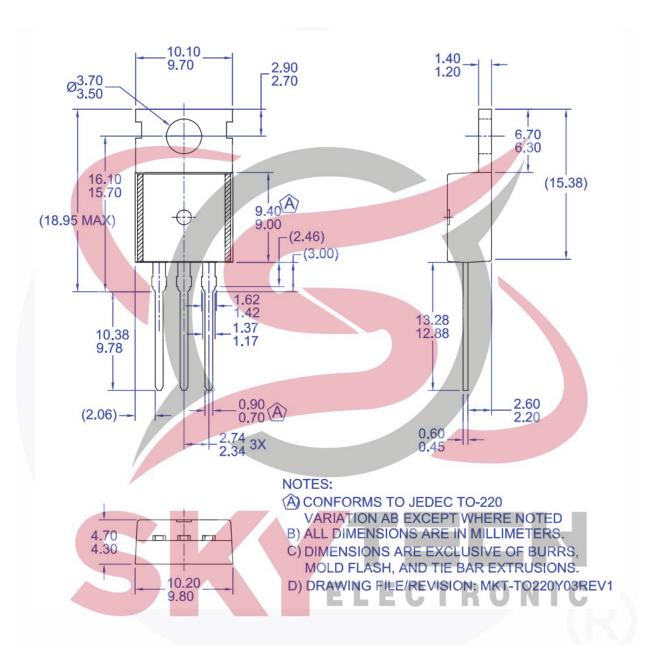


Figure 16. TO220, Molded, 3-Lead, Jedec Variation AB

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